실리콘 표준공정 기준단가 (2017년도)

장비명	공 정 명	Code	B/Size	단가 (단위:원)	
			(wfs)	기준단가	외부(기준*80%))
Cleaning & Strip(Wet)	Cleaning DIW	WT01/02	25	40,000	32,000
	Cleaning STD1	WT03	25	50,000	40,000
	Cleaning STD3	WT03	25	50,000	40,000
	Cleaning SC1	WT03	25	50,000	40,000
	Cleaning10 :1HF	WT02	25	50,000	40,000
	Cleaning H2SO4	WT03	25	50,000	40,000
	Cleaning 100:1 HF / 50:1HF	WT04	25	50,000	40,000
	Acid Strip(H3PO4)	WT05	25	50,000	40,000
	Wet Etch (Lal 1000, 7:1 BHF)	WT02	25	50,000	40,000
	Deglaze	WT02	25	50,000	40,000
	Al Etchant	WT05	25	50,000	40,000
	TiW, TiN Wet Etch	WT05	25	50,000	40,000
	Cleaning SC1	SW01	1	10,000	8,000
	Cleaning 10:1 HF	SW01	1	10,000	8,000
Furnace	Oxidation(T<=1900A)	FN12/22	25	220,000	176,000
	Oxidation(1900<T<=5000A)	FN12/22	25	320,000	256,000
	Oxidation(>5000A)	FN12/22	25	460,000	368,000
	Drive-In & Oxidation(<5000A)	FN12/22	25	600,000	480,000
	Drive-In(<=1hr)	FN12/22	25	120,000	96,000
	Drive-In(1hr<Time<3hr)	FN12/22	25	210,000	168,000
	Drive-In(3hr<Time<5hr)	FN12/22	25	260,000	208,000
	Drive-In(5hr<Time<=7hr)	FN12/22	25	310,000	248,000
	Drive-In(7hr<Time<=10hr)	FN12/22	25	360,000	288,000
	Drive-In(10hr<Time<=13hr)	FN12/22	25	420,000	336,000
	Drive-In(13hr<Time<=16hr)	FN12/22	25	600,000	480,000
	Drive-In(16hr<Time<=20hr)	FN12/22	25	800,000	640,000
	POC13 Doping	FN21	25	200,000	160,000
	Anneal	FN12/22	25	120,000	96,000
	Alloy/SOG Curing/Dehydrate	FN11	25	120,000	96,000
	RTA	RT01	1	40,000	32,000
LPCVD	LP TEOX(T<=5000A)	LP34	25	220,000	176,000
	LP TEOX(5000<T<=10000A)	LP34	25	240,000	192,000
	LP TEOX(>=10000A)	LP34	25	280,000	224,000
	LP Nitride(T<=1600A)	LP33	25	220,000	176,000
	LP Nitride(1600<T<=3000A)	LP33	25	240,000	192,000
	Poly Si(T<=5000A)	LP32	25	270,000	216,000
	Poly Si(5000<T<=8000A)	LP32	25	300,000	240,000
	Poly Si(8000<T<=15000A)	LP32	25	350,000	280,000
	LP LTOX(<=5000A)	LP31	25	280,000	224,000
	LP LTOX(5000<T<=10000A)	LP31	25	300,000	240,000
	SOG (1000<T<=5000A)	SC01	1	120,000	96,000
PECVD	PE OX(T<=5000A)	PE02/DR05	1	40,000	32,000
	PE OX(5000<T<=10000A)	PE02/DR05	1	50,000	40,000
	PE Ge-OX(T<=20000A)	DR05	1	120,000	96,000
	PE Nitride(T<=5000A)	PE02/DR05	1	50,000	40,000
	PE Nitride(5000<T<=10000A)	PE02/DR05	1	60,000	48,000
	SACVD BPSG(T<=5000A)	PE02	1	60,000	48,000
	SACVD BPSG(5000<T<=10000A)	PE02	1	80,000	64,000
	SACVD BPSG(10000<T<=20000A)	PE02	1	140,000	112,000
	SACVD BPSG(20000<T<=30000A)	PE02	1	210,000	168,000
	PE TEOS(T<=5000A)	PE02	1	40,000	32,000
	PE TEOS(5000<T<=10000A)	PE02	1	60,000	48,000
	PE Oxynitride(T<=5000A)	PE02	1	50,000	40,000
	PE Oxynitride(5000<T<=10000A)	PE02	1	70,000	56,000
Implant	AS, P, BF2 (>=1E15)	IM02	17	595,000	476,000
	P, BF2, B11 (<=1E14)	IM01	1	30,000	24,000
	Nitride(T<=2000A)	DR03	1	40,000	32,000
	Nitride(2000<T<=3000A)	DR03	1	50,000	40,000

장비명	공 정 명	Code	B/Size	단가 (단위:원)	
			(wfs)	기준단가	외부(기준*80%))
Dry etch	Nitride(3000<T<=7000A)	DR03	1	60,000	48,000
	Poly(<=3000A)	DR03	1	40,000	32,000
	Poly(3000<T<=7000A)	DR03	1	70,000	56,000
	Poly(7000<T<=10000A)	DR03	1	80,000	64,000
	Oxide(<=3000A)	DR03/05/06	1	40,000	32,000
	Oxide(3000<T<=7000A)	DR03/05/06	1	50,000	40,000
	Oxide(7000A<T<=15000A)	DR03/05/06	1	70,000	56,000
	Silicon(3000<T<=7000A)	DR03	1	70,000	56,000
	Silicon(7000<T<=10000A)	DR03	1	90,000	72,000
	Silicon(10000<T<=25000A)	DR03	1	110,000	88,000
	Silicon(2.5um<T<=4umA)	DR03	1	140,000	112,000
	Silicon residue remove (< 500A)	DR03/DR06	1	30,000	24,000
	Planar	DR03	1	30,000	24,000
	Metal(AlSi T<=10000A)	DR05/06	1	40,000	32,000
	Metal(AlSi 10000<T<=20000A)	DR05/06	1	60,000	48,000
	Metal(AlSi T>20000A)	DR05/06	1	70,000	56,000
	Metal(TiW/AlSi/TiW)	DR05/06	1	50,000	40,000
	Metal(Ti/AlSi/TiN)	DR05/06	1	50,000	40,000
	TiW(Pad)	DR05/06	1	30,000	24,000
	ITO etch	DR05/06	1	100,000	80,000
	MO etch	DR05/06	1	100,000	80,000
	CMP Poly (T<=10000A)	CM01	1	50,000	40,000
	CMP Poly (10000A<T<=20000A)	CM01	1	70,000	56,000
	CMP Poly (20000A<T<=40000A)	CM01	1	90,000	72,000
	CMP Oxide (T<=10000A)	CM01	1	50,000	40,000
	CMP Oxide (10000A<T<=20000A)	CM01	1	80,000	64,000
	CMP Oxide (20000A<T<=40000A)	CM01	1	90,000	72,000
	HD etch oxide(<=3000A)	DR07	1	60,000	48,000
	HD etch oxide(3000<T<=7000A)	DR07	1	70,000	56,000
	HD etch oxide(7000A<T<=15000A)	DR07	1	90,000	72,000
	HD etch Nitride(<=2000A)	DR07	1	50,000	40,000
	HD etch Nitride(2000A<T<=3000 A)	DR07	1	60,000	48,000
	HD etch Nitride(3000A<T<=7000A)	DR07	1	70,000	56,000
	HD Poly(<=3000A)	DR07	1	50,000	40,000
	HD Poly(3000<T<=7000A)	DR07	1	80,000	64,000
	HD Poly(7000<T<=10000A)	DR07	1	90,000	72,000
	HD Silicon(3000<T<=7000A)	DR07	1	80,000	64,000
	HD Silicon(7000<T<=10000A)	DR07	1	100,000	80,000
	HD Silicon(10000<T<=25000A)	DR07	1	120,000	96,000
Photo	HMDS	TR01/02	1	5,000	4,000
	EBR	TR01/02	1	5,000	4,000
	HMDS/Coat/EBR/Bake	TR01/02	1	15,000	12,000
	Exposure (i-line Stepper)	ST02,3	1	20,000	16,000
	Exposure(Projection Aligner)	PA01	1	15,000	12,000
	Bake PEB	TR01/02	1	5,000	4,000
	PEB/Develop (time ≤90 sec)	TR01/02	1	15,000	12,000
	PEB/Develop (time >90 sec)	TR01/02	1	20,000	16,000
	Bake Hard	OV03	25	15,000	12,000
	Mask Tooling (<=4hr)	MT-1	4hr	200,000	160,000
	TiW/Al/TiW Depo.	SP01/03	1	80,000	64,000
	TiW Dep.(T<=3000A)	SP01/03	1	40,000	32,000
	TiW Dep.(T>3000A)	SP01/03	1	50,000	40,000
	Si(N) Dep.(<=5000A)	SP01	1	40,000	32,000
	Si(N) Dep.(5000<T<=10000A)	SP01	1	50,000	40,000
	Si(P) Dep.(<=5000A)	SP01	1	30,000	24,000
	Si(P) Dep.(5000<T<=10000A)	SP01	1	50,000	40,000
	Ni Dep.(<=500A)	SP01	1	30,000	24,000
	Ni Dep.(500<T<=1000A)	SP01	1	50,000	40,000
	Ti Dep.(<=2000A)	SP02	1	30,000	24,000
	Ti Dep.(>2000A)	SP02	1	50,000	40,000

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			(wfs)	기준단가	외부(기준*80%))
Spurttering	TiN Dep.(<=2000A)	SP02	1	30,000	24,000
	TiN Dep.(>2000A)	SP02	1	50,000	40,000
	Al Dep.(<=10000A)	SP01/02/03	1	30,000	24,000
	Al Dep.(10000<T<=20000A)	SP01/02/03	1	50,000	40,000
	Al Dep.(>=20000A)	SP01/02/03	1	70,000	56,000
	Al/TiN Dep.	SP02	1	60,000	48,000
	Ti/TiN Dep.	SP02	1	60,000	48,000
	Ti/Al/TiN Dep.	SP02	1	90,000	72,000
	MO Dep.	SP02	1	100,000	80,000
	Alloy M2i	SP02	1	50,000	40,000
	Al (1um이하)	EP01	5	300,000	240,000
	Ti/Ni/Ag	EP01	5	300,000	240,000
PR Strip	Dry Strip1,	PS01/PS03	25	50,000	40,000
	Dry Strip3	DR05/06	1	5,000	4,000
	Acid	WT02	25	40,000	32,000
	Descum1	PS02	1	5,000	4,000
	Descum2	DR03	1	5,000	4,000
	Solvent Strip	WT01	25	40,000	32,000
	NMD-3(Polymer removal)	TR01/02	1	20,000	16,000
	Micro-Wave strip	PS02	1	5,000	4,000
	RIE strip	PS02	1	5,000	4,000
Measure	CD Measure	CD	1	40,000	32,000
	Rs Measure	4-P	1	5,000	4,000
	Inspection	Scope	1	3,000	2,400
	Film Thickness	NS02	1	10,000	8,000
Marking	Laser Marking	LM01	1	2,000	1,600

(1) 기준 단가표에 없는 공정 단가는 외삽법에 의한다.

(2) CD Measure 장비사용 단가는 매 30min 초과시 1장 (기준 시간 30분)씩 계상하는 방식으로 수정

(3) 정부지원사업을 통한 제품 제작 (학계, 연구소 등) 및 대기업은 기준 단가를 적용

(4) 외부(중소.벤처) 지원단가(천원이하 천원으로 절사)

(4)-1. 공정 비용 적용은 기준 단가의 80%(단 기준단가 60만원 이하일 경우 100% 적용),
양산 경우는 계약 volume에 따라 할인율 적용

(4)-2. 계약 volume 적용 할인율

- 6000만원 미만 : 기준 단가의 80%
- 6000만원 이상 ~ 1억원 미만 : 기준 단가의 50%
- 1억원 이상 ~ 5억원 미만 : 기준 단가의 45%
- 5억원 이상 ~ 10억원 미만 : 기준 단가의 40%
- 10억원 이상 ~ 16.7억원 미만 : 기준 단가의 35%
- 16.7억원 이상 : 기준 단가의 30%